

DATA SHEET

74LVC2G241

Dual buffer/line driver with 5 V
tolerant inputs/outputs; 3-state

Product specification
Supersedes data of 2003 Jan 29

2003 Mar 11

Dual buffer/line driver with 5 V tolerant inputs/outputs; 3-state

74LVC2G241

FEATURES

- Wide supply voltage range from 1.65 to 5.5 V
- 5 V tolerant input/output for interfacing with 5 V logic
- High noise immunity
- Complies with JEDEC standard:
 - JESD8-7 (1.65 to 1.95 V)
 - JESD8-5 (2.3 to 2.7 V)
 - JESD8B/JESD36 (2.7 to 3.6 V).
- ± 24 mA output drive ($V_{CC} = 3.0$ V)
- CMOS low power consumption
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- ESD protection:
HBM EIA/JESD22-A114-A exceeds 2000 V
MM EIA/JESD22-A115-A exceeds 200 V.
- Specified from -40 to $+85$ °C and -40 to $+125$ °C.

DESCRIPTION

The 74LVC2G241 is a high-performance, low-power, low-voltage, Si-gate CMOS device and superior to most advanced CMOS compatible TTL families.

Inputs can be driven from either 3.3 or 5 V devices. This feature allows the use of these devices as translators in a mixed 3.3 and 5 V environment.

This device is fully specified for partial power-down applications using I_{off} . The I_{off} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

The 74LVC2G241 is a dual non-inverting buffer/line driver with 3-state outputs. The 3-state outputs are controlled by the output enable inputs $1OE$ and $2OE$. A HIGH level at pin $1OE$ causes output $1Y$ to assume a high-impedance OFF-state. A LOW level at pin $2OE$ causes output $2Y$ to assume a high-impedance OFF-state. Schmitt-trigger action at all inputs makes the circuit highly tolerant for slower input rise and fall times.

QUICK REFERENCE DATA

GND = 0 V; $T_{amb} = 25$ °C.

SYMBOL	PARAMETER	CONDITIONS	TYPICAL	UNIT
t_{PHL}/t_{PLH}	propagation delay inputs nA to output nY	$V_{CC} = 1.8$ V; $C_L = 30$ pF; $R_L = 1$ k Ω	4.5	ns
		$V_{CC} = 2.5$ V; $C_L = 30$ pF; $R_L = 500$ Ω	2.8	ns
		$V_{CC} = 2.7$ V; $C_L = 50$ pF; $R_L = 500$ Ω	2.8	ns
		$V_{CC} = 3.3$ V; $C_L = 50$ pF; $R_L = 500$ Ω	2.6	ns
		$V_{CC} = 5.0$ V; $C_L = 50$ pF; $R_L = 500$ Ω	2.1	ns
C_I	input capacitance		2	pF
C_{PD}	power dissipation capacitance per buffer	output enabled; notes 1 and 2	20	pF
		output disabled; notes 1 and 2	5	pF

Notes

1. C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in Volts;

N = total switching outputs;

$\sum (C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

2. The condition is $V_I = \text{GND to } V_{CC}$.

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FUNCTION TABLE

See note 1.

INPUT				OUTPUT	
1OE	1A	2OE	2A	1Y	2Y
L	L	H	L	L	L
L	H	H	H	H	H
H	X	L	X	Z	Z

Note

1. H = HIGH voltage level;
L = LOW voltage level;
X = don't care;
Z = high-impedance OFF-state.

ORDERING INFORMATION

TYPE NUMBER	TEMPERATURE RANGE	PACKAGE				
		PINS	PACKAGE	MATERIAL	CODE	MARKING
74LVC2G241DP	−40 to +125 °C	8	TSSOP8	plastic	SOT505-2	V241
74LVC2G241DC	−40 to +125 °C	8	VSSOP8	plastic	SOT765-1	V41

PINNING

PIN	SYMBOL	DESCRIPTION
1	1OE	output enable input (active LOW)
2	1A	data input
3	2Y	data output
4	GND	ground (0 V)
5	2A	data input
6	1Y	data output
7	2OE	output enable input (active HIGH)
8	V _{CC}	supply voltage

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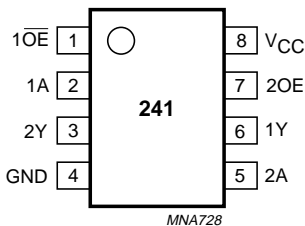


Fig.1 Pin configuration.

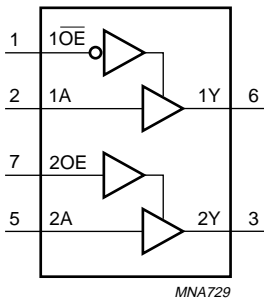


Fig.2 Logic symbol.

Dual buffer/line driver with 5 V tolerant inputs/outputs; 3-state

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RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CC}	supply voltage		1.65	5.5	V
V_I	input voltage		0	5.5	V
V_O	output voltage	$V_{CC} = 1.65$ to 5.5 V; enable mode	0	V_{CC}	V
		$V_{CC} = 1.65$ to 5.5 V; disable mode	0	5.5	V
		$V_{CC} = 0$ V; Power-down mode	0	5.5	V
T_{amb}	operating ambient temperature		-40	+125	°C
t_r, t_f	input rise and fall times	$V_{CC} = 1.65$ to 2.7 V	0	20	ns/V
		$V_{CC} = 2.7$ to 5.5 V	0	10	ns/V

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134); voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CC}	supply voltage		-0.5	+6.5	V
I_{IK}	input diode current	$V_I < 0$	–	-50	mA
V_I	input voltage	note 1	-0.5	+6.5	V
I_{OK}	output diode current	$V_O > V_{CC}$ or $V_O < 0$	–	±50	mA
V_O	output voltage	enable mode; notes 1 and 2	-0.5	$V_{CC} + 0.5$	V
		disable mode; notes 1 and 2	-0.5	+6.5	V
		Power-down mode; notes 1 and 2	-0.5	+6.5	V
I_O	output source or sink current	$V_O = 0$ to V_{CC}	–	±50	mA
I_{CC}, I_{GND}	V_{CC} or GND current		–	±100	mA
T_{stg}	storage temperature		-65	+150	°C
P_D	power dissipation	$T_{amb} = -40$ to $+125$ °C; note 3	–	300	mW

Notes

1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. When $V_{CC} = 0$ V (Power-down mode), the output voltage can be 5.5 V in normal operation.
3. Above 110 °C the value of P_D derates linearly with 8 mW/K.

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DC CHARACTERISTICS

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	TEST CONDITIONS		MIN.	TYP. ⁽¹⁾	MAX.	UNIT
		OTHER	V _{CC} (V)				
T _{amb} = −40 to +85 °C							
V _{IH}	HIGH-level input voltage		1.65 to 1.95	0.65 × V _{CC}	–	–	V
			2.3 to 2.7	1.7	–	–	V
			2.7 to 3.6	2.0	–	–	V
			4.5 to 5.5	0.7 × V _{CC}	–	–	V
V _{IL}	LOW-level input voltage		1.65 to 1.95	–	–	0.35 × V _{CC}	V
			2.3 to 2.7	–	–	0.7	V
			2.7 to 3.6	–	–	0.8	V
			4.5 to 5.5	–	–	0.3 × V _{CC}	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} I _O = 100 μA I _O = 4 mA I _O = 8 mA I _O = 12 mA I _O = 24 mA I _O = 32 mA	1.65 to 5.5	–	–	0.1	V
			1.65	–	–	0.45	V
			2.3	–	–	0.3	V
			2.7	–	–	0.4	V
			3.0	–	–	0.55	V
			4.5	–	–	0.55	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} I _O = −100 μA I _O = −4 mA I _O = −8 mA I _O = −12 mA I _O = −24 mA I _O = −32 mA	1.65 to 5.5	V _{CC} − 0.1	–	–	V
			1.65	1.2	–	–	V
			2.3	1.9	–	–	V
			2.7	2.2	–	–	V
			3.0	2.3	–	–	V
			4.5	3.8	–	–	V
I _{LI}	input leakage current	V _I = 5.5 V or GND	5.5	–	±0.1	±5	μA
I _{OZ}	3-state output OFF-state current	V _I = V _{IH} or V _{IL} ; V _O = 5.5 V or GND	3.6	–	±0.1	±10	μA
I _{off}	power OFF leakage current	V _I or V _O = 5.5 V	0	–	±0.1	±10	μA
I _{CC}	quiescent supply current	V _I = V _{CC} or GND; I _O = 0	5.5	–	0.1	10	μA
ΔI _{CC}	additional quiescent supply current per pin	V _I = V _{CC} − 0.6 V; I _O = 0	2.3 to 5.5	–	5	500	μA

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SYMBOL	PARAMETER	TEST CONDITIONS		MIN.	TYP. ⁽¹⁾	MAX.	UNIT
		OTHER	V _{CC} (V)				
T _{amb} = −40 to +125 °C							
V _{IH}	HIGH-level input voltage		1.65 to 1.95	0.65 × V _{CC}	—	—	V
			2.3 to 2.7	1.7	—	—	V
			2.7 to 3.6	2.0	—	—	V
			4.5 to 5.5	0.7 × V _{CC}	—	—	V
V _{IL}	LOW-level input voltage		1.65 to 1.95	—	—	0.35 × V _{CC}	V
			2.3 to 2.7	—	—	0.7	V
			2.7 to 3.6	—	—	0.8	V
			4.5 to 5.5	—	—	0.3 × V _{CC}	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}					
		I _O = 100 μA	1.65 to 5.5	—	—	0.1	V
		I _O = 4 mA	1.65	—	—	0.70	V
		I _O = 8 mA	2.3	—	—	0.45	V
		I _O = 12 mA	2.7	—	—	0.60	V
		I _O = 24 mA	3.0	—	—	0.80	V
		I _O = 32 mA	4.5	—	—	0.80	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}					
		I _O = −100 μA	1.65 to 5.5	V _{CC} − 0.1	—	—	V
		I _O = −4 mA	1.65	0.95	—	—	V
		I _O = −8 mA	2.3	1.7	—	—	V
		I _O = −12 mA	2.7	1.9	—	—	V
		I _O = −24 mA	3.0	2.0	—	—	V
		I _O = −32 mA	4.5	3.4	—	—	V
I _{LI}	input leakage current	V _I = 5.5 V or GND	5.5	—	—	±20	μA
I _{OZ}	3-state output OFF-state current	V _I = V _{IH} or V _{IL} ; V _O = 5.5 V or GND	3.6	—	—	±20	μA
I _{off}	power OFF leakage current	V _I or V _O = 5.5 V	0	—	—	±20	μA
I _{CC}	quiescent supply current	V _I = V _{CC} or GND; I _O = 0	5.5	—	—	40	μA
ΔI _{CC}	additional quiescent supply current per pin	V _I = V _{CC} − 0.6 V; I _O = 0	2.3 to 5.5	—	—	5000	μA

Note

1. All typical values are measured at V_{CC} = 3.3 V and T_{amb} = 25 °C.

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AC CHARACTERISTICS

GND = 0 V.

SYMBOL	PARAMETER	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
		WAVEFORMS	V _{CC} (V)				
T _{amb} = −40 to +85 °C; note 1							
t _{PHL} /t _{PLH}	propagation delay nA to nY	see Figs 3 and 6	1.65 to 1.95	1.0	4.5	8.8	ns
			2.3 to 2.7	0.5	2.8	4.9	ns
			2.7	1.0	2.8	4.7	ns
			3.0 to 3.6	0.5	2.6	4.3	ns
			4.5 to 5.5	0.5	2.1	3.7	ns
t _{PZH} /t _{PZL}	3-state output enable time 1OE to 1Y	see Figs 4 and 6	1.65 to 1.95	1.5	5.2	9.9	ns
			2.3 to 2.7	1.0	3.1	5.6	ns
			2.7	1.5	3.2	5.5	ns
			3.0 to 3.6	0.5	2.7	4.7	ns
			4.5 to 5.5	0.5	2.0	3.8	ns
t _{PHZ} /t _{PLZ}	3-state output disable time 1OE to 1Y	see Figs 4 and 6	1.65 to 1.95	1.0	3.2	11.6	ns
			2.3 to 2.7	0.5	2.2	5.8	ns
			2.7	1.0	2.8	4.6	ns
			3.0 to 3.6	1.0	2.6	4.4	ns
			4.5 to 5.5	0.5	2.0	3.4	ns
t _{PZH} /t _{PZL}	3-state output enable time 2OE to 2Y	see Figs 5 and 6	1.65 to 1.95	1.0	4.3	8.8	ns
			2.3 to 2.7	1.0	2.7	4.7	ns
			2.7	1.0	2.7	4.6	ns
			3.0 to 3.6	1.0	2.5	4.1	ns
			4.5 to 5.5	0.5	1.9	3.3	ns
t _{PHZ} /t _{PLZ}	3-state output disable time 2OE to 2Y	see Figs 5 and 6	1.65 to 1.95	1.0	3.6	12.5	ns
			2.3 to 2.7	0.5	2.0	5.2	ns
			2.7	1.5	3.2	4.9	ns
			3.0 to 3.6	1.0	2.8	4.2	ns
			4.5 to 5.5	0.5	2.0	3.3	ns

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SYMBOL	PARAMETER	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
		WAVEFORMS	V _{CC} (V)				
T _{amb} = −40 to +125 °C							
t _{PHL} /t _{PLH}	propagation delay nA to nY	see Figs 3 and 6	1.65 to 1.95	1.0	—	11.0	ns
			2.3 to 2.7	0.5	—	6.3	ns
			2.7	1.0	—	5.9	ns
			3.0 to 3.6	0.5	—	5.4	ns
			4.5 to 5.5	0.5	—	4.6	ns
t _{PZH} /t _{PZL}	3-state output enable time 1 $\overline{\text{OE}}$ to 1Y	see Figs 4 and 6	1.65 to 1.95	1.5	—	12.4	ns
			2.3 to 2.7	1.0	—	7.0	ns
			2.7	1.5	—	6.9	ns
			3.0 to 3.6	0.5	—	5.9	ns
			4.5 to 5.5	0.5	—	4.8	ns
t _{PHZ} /t _{PLZ}	3-state output disable time 1 $\overline{\text{OE}}$ to 1Y	see Figs 4 and 6	1.65 to 1.95	1.0	—	14.1	ns
			2.3 to 2.7	0.5	—	7.6	ns
			2.7	1.0	—	5.9	ns
			3.0 to 3.6	1.0	—	5.7	ns
			4.5 to 5.5	0.5	—	4.6	ns
t _{PZH} /t _{PZL}	3-state output enable time 2OE to 2Y	see Figs 5 and 6	1.65 to 1.95	1.0	—	11.0	ns
			2.3 to 2.7	1.0	—	5.9	ns
			2.7	1.0	—	5.8	ns
			3.0 to 3.6	1.0	—	5.1	ns
			4.5 to 5.5	0.5	—	4.1	ns
t _{PHZ} /t _{PLZ}	3-state output disable time 2OE to 2Y	see Figs 5 and 6	1.65 to 1.95	1.0	—	15.2	ns
			2.3 to 2.7	0.5	—	6.9	ns
			2.7	1.5	—	6.3	ns
			3.0 to 3.6	1.0	—	5.4	ns
			4.5 to 5.5	0.5	—	4.4	ns

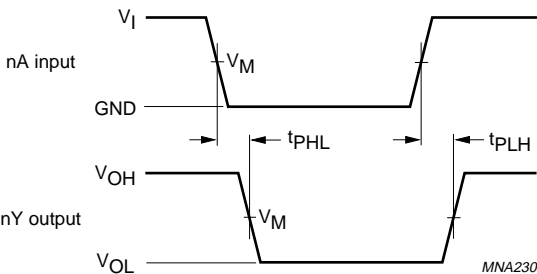
Note

1. All typical values are measured at T_{amb} = 25 °C.

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AC WAVEFORMS



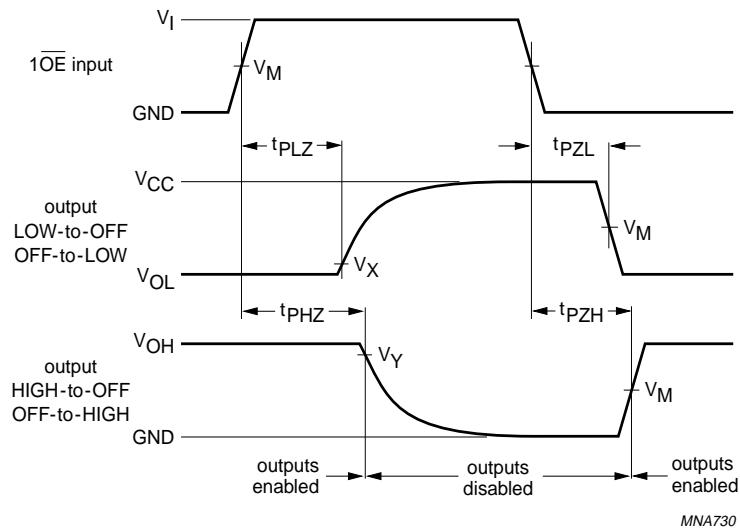
V_{CC}	V_M	INPUT	
		V_I	$t_r = t_f$
1.65 to 1.95 V	$0.5 \times V_{CC}$	V_{CC}	≤ 2.0 ns
2.3 to 2.7 V	$0.5 \times V_{CC}$	V_{CC}	≤ 2.0 ns
2.7 V	1.5 V	2.7 V	≤ 2.5 ns
3.0 to 3.6 V	1.5 V	2.7 V	≤ 2.5 ns
4.5 to 5.5 V	$0.5 \times V_{CC}$	V_{CC}	≤ 2.5 ns

V_{OL} and V_{OH} are typical output voltage drop that occur with the output load.

Fig.3 The input (nA) to output (nY) propagation delays and the output transition times.

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V _{CC}	V _M	INPUT	
		V _I	t _r = t _f
1.65 to 1.95 V	0.5 × V _{CC}	V _{CC}	≤ 2.0 ns
2.3 to 2.7 V	0.5 × V _{CC}	V _{CC}	≤ 2.0 ns
2.7 V	1.5 V	2.7 V	≤ 2.5 ns
3.0 to 3.6 V	1.5 V	2.7 V	≤ 2.5 ns
4.5 to 5.5 V	0.5 × V _{CC}	V _{CC}	≤ 2.5 ns

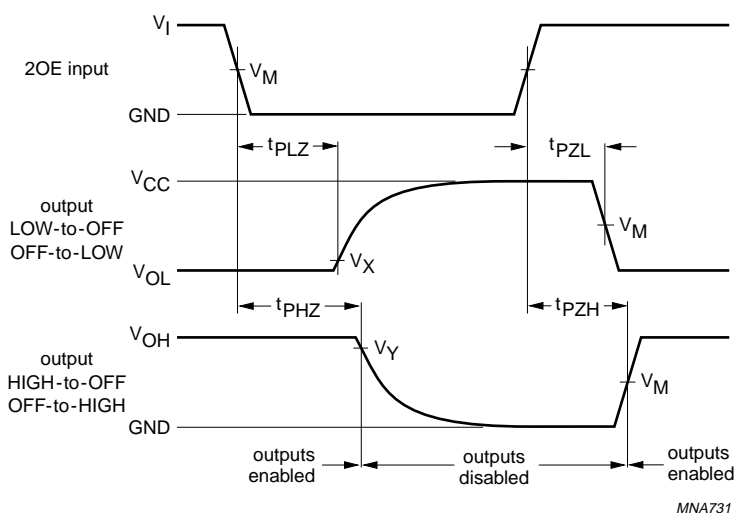
V_X = V_{OL} + 0.3 V at V_{CC} ≥ 2.7 V;
V_X = V_{OL} + 0.15 V at V_{CC} < 2.7 V;
V_Y = V_{OH} - 0.3 V at V_{CC} ≥ 2.7 V;
V_Y = V_{OH} - 0.15 V at V_{CC} < 2.7 V.

V_{OL} and V_{OH} are typical output voltage drop that occur with the output load.

Fig.4 3-state enable and disable times for input 1OE.

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V_{CC}	V_M	INPUT	
		V_I	$t_r = t_f$
1.65 to 1.95 V	$0.5 \times V_{CC}$	V_{CC}	≤ 2.0 ns
2.3 to 2.7 V	$0.5 \times V_{CC}$	V_{CC}	≤ 2.0 ns
2.7 V	1.5 V	2.7 V	≤ 2.5 ns
3.0 to 3.6 V	1.5 V	2.7 V	≤ 2.5 ns
4.5 to 5.5 V	$0.5 \times V_{CC}$	V_{CC}	≤ 2.5 ns

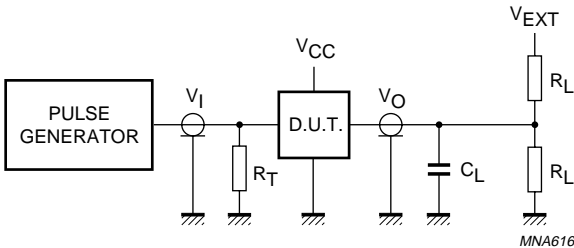
$$V_X = V_{OL} + 0.3 \text{ V at } V_{CC} \geq 2.7 \text{ V};$$
$$V_X = V_{OL} + 0.15 \text{ V at } V_{CC} < 2.7 \text{ V};$$
$$V_Y = V_{OH} - 0.3 \text{ V at } V_{CC} \geq 2.7 \text{ V;}$$
$$V_Y = V_{OH} - 0.15 \text{ V at } V_{CC} < 2.7 \text{ V.}$$

V_{OL} and V_{OH} are typical output voltage drop that occur with the output load.

Fig.5 3-state enable and disable times for input 2OE.

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V _{CC}	V _I	C _L	R _L	V _{EXT}		
				t _{PLH} /t _{PHL}	t _{PZH} /t _{PHZ}	t _{PZL} /t _{PLZ}
1.65 to 1.95 V	V _{CC}	30 pF	1 kΩ	open	GND	2 × V _{CC}
2.3 to 2.7 V	V _{CC}	30 pF	500 Ω	open	GND	2 × V _{CC}
2.7 V	2.7 V	50 pF	500 Ω	open	GND	6 V
3.0 to 3.6 V	2.7 V	50 pF	500 Ω	open	GND	6 V
4.5 to 5.5 V	V _{CC}	50 pF	500 Ω	open	GND	2 × V _{CC}

Definitions for test circuit:
R_L = Load resistor.
C_L = Load capacitance including jig and probe capacitance.
R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

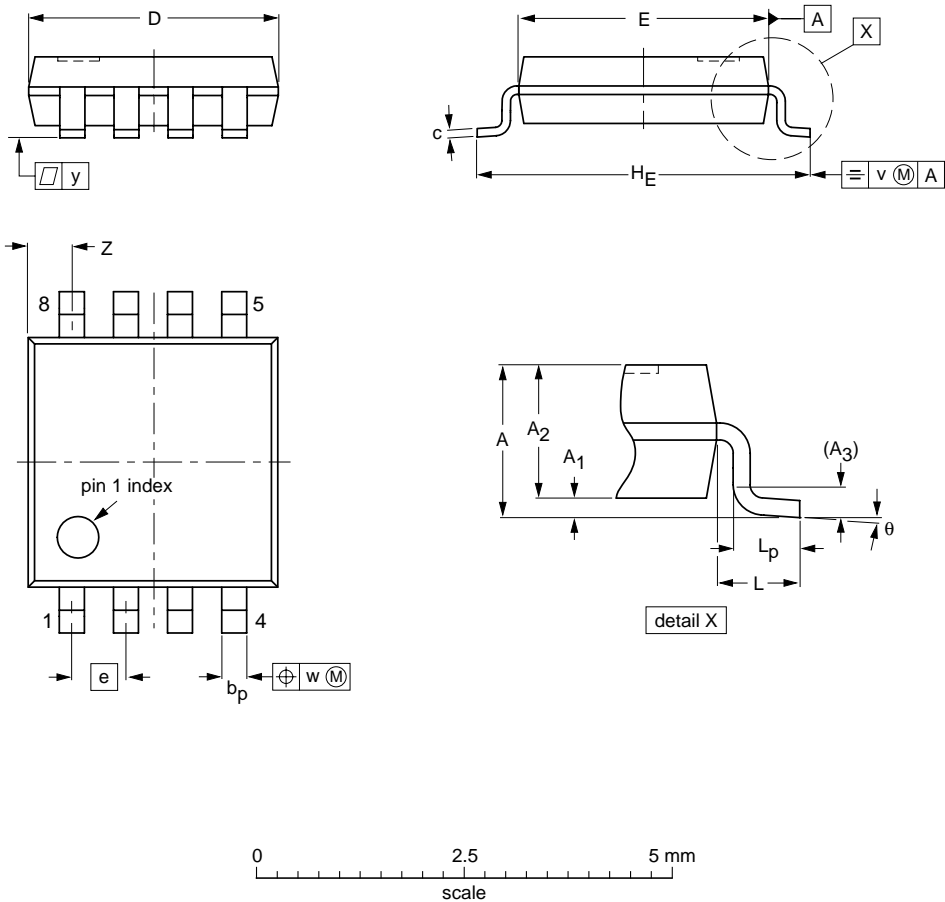
Fig.6 Load circuitry for switching times.

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PACKAGE OUTLINES

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽¹⁾	e	H _E	L	L _p	v	w	y	Z ⁽¹⁾	θ
mm	1.1	0.15 0.00	0.95 0.75	0.25	0.38 0.22	0.18 0.08	3.1 2.9	3.1 2.9	0.65	4.1 3.9	0.5	0.47 0.33	0.2	0.13	0.1	0.70 0.35	8° 0°

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

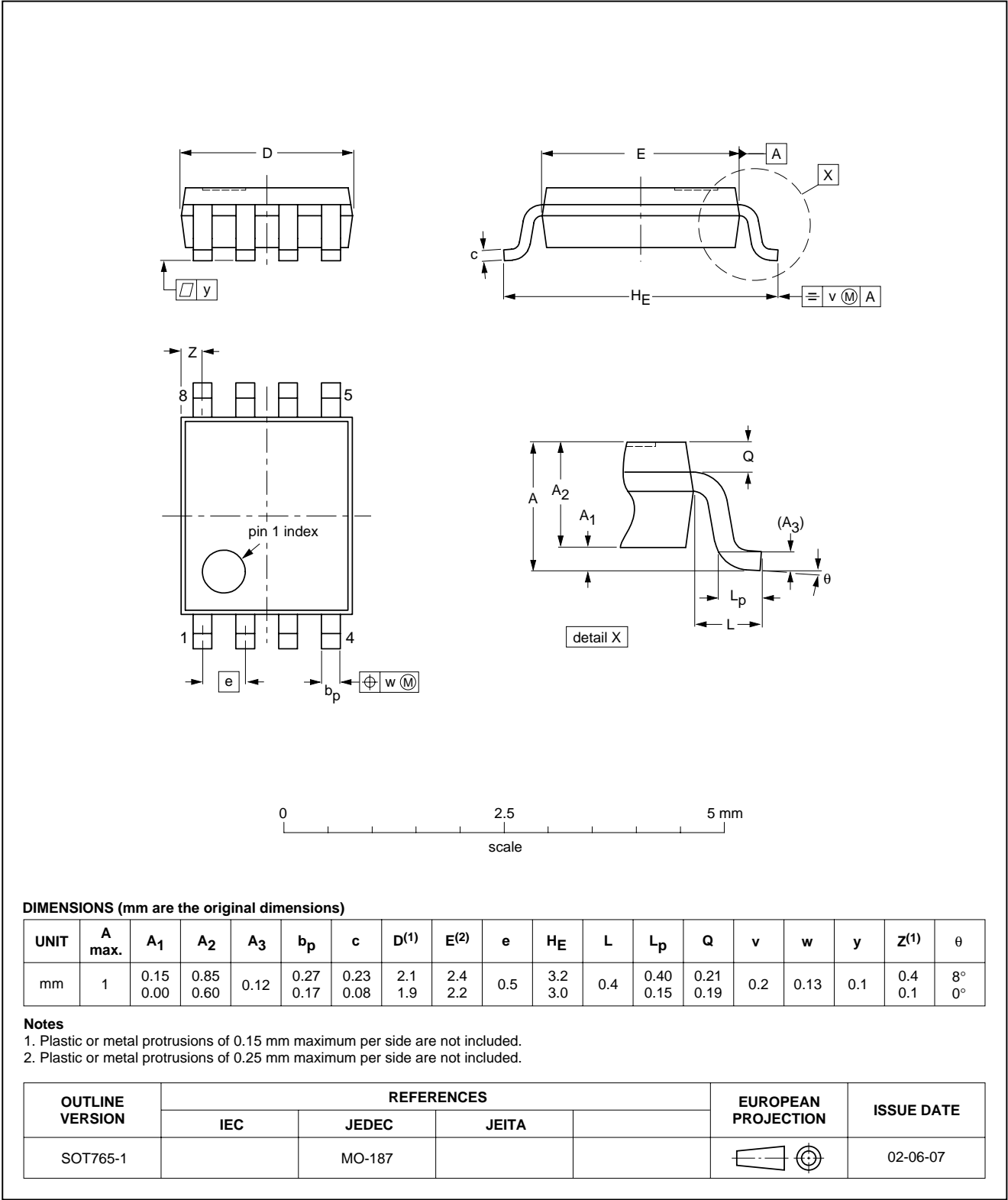
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT505-2		---				02-01-16

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VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1



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SOLDERING

Introduction to soldering surface mount packages

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our *"Data Handbook IC26; Integrated Circuit Packages"* (document order number 9398 652 90011).

There is no soldering method that is ideal for all surface mount IC packages. Wave soldering can still be used for certain surface mount ICs, but it is not suitable for fine pitch SMDs. In these situations reflow soldering is recommended.

Reflow soldering

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several methods exist for reflowing; for example, convection or convection/infrared heating in a conveyor type oven. Throughput times (preheating, soldering and cooling) vary between 100 and 200 seconds depending on heating method.

Typical reflow peak temperatures range from 215 to 250 °C. The top-surface temperature of the packages should preferably be kept:

- below 220 °C for all the BGA packages and packages with a thickness ≥ 2.5 mm and packages with a thickness < 2.5 mm and a volume ≥ 350 mm³ so called thick/large packages
- below 235 °C for packages with a thickness < 2.5 mm and a volume < 350 mm³ so called small/thin packages.

Wave soldering

Conventional single wave soldering is not recommended for surface mount devices (SMDs) or printed-circuit boards with a high component density, as solder bridging and non-wetting can present major problems.

To overcome these problems the double-wave soldering method was specifically developed.

If wave soldering is used the following conditions must be observed for optimal results:

- Use a double-wave soldering method comprising a turbulent wave with high upward pressure followed by a smooth laminar wave.
- For packages with leads on two sides and a pitch (e):
 - larger than or equal to 1.27 mm, the footprint longitudinal axis is **preferred** to be parallel to the transport direction of the printed-circuit board;
 - smaller than 1.27 mm, the footprint longitudinal axis **must** be parallel to the transport direction of the printed-circuit board.

The footprint must incorporate solder thieves at the downstream end.

- For packages with leads on four sides, the footprint must be placed at a 45° angle to the transport direction of the printed-circuit board. The footprint must incorporate solder thieves downstream and at the side corners.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Typical dwell time is 4 seconds at 250 °C.

A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

Manual soldering

Fix the component by first soldering two diagonally-opposite end leads. Use a low voltage (24 V or less) soldering iron applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300 °C.

When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 °C.

Dual buffer/line driver with 5 V tolerant inputs/outputs; 3-state

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Suitability of surface mount IC packages for wave and reflow soldering methods

PACKAGE ⁽¹⁾	SOLDERING METHOD	
	WAVE	REFLOW ⁽²⁾
BGA, LBGA, LFBGA, SQFP, TFBGA, VFBGA	not suitable	suitable
DHVQFN, HBCC, HBGA, HLQFP, HSQFP, HSOP, HTQFP, HTSSOP, HVQFN, HVSON, SMS	not suitable ⁽³⁾	suitable
PLCC ⁽⁴⁾ , SO, SOJ	suitable	suitable
LQFP, QFP, TQFP	not recommended ⁽⁴⁾⁽⁵⁾	suitable
SSOP, TSSOP, VSO, VSSOP	not recommended ⁽⁶⁾	suitable

Notes

- For more detailed information on the BGA packages refer to the “(LF)BGA Application Note” (AN01026); order a copy from your Philips Semiconductors sales office.
- All surface mount (SMD) packages are moisture sensitive. Depending upon the moisture content, the maximum temperature (with respect to time) and body size of the package, there is a risk that internal or external package cracks may occur due to vaporization of the moisture in them (the so called popcorn effect). For details, refer to the Drypack information in the “Data Handbook IC26; Integrated Circuit Packages; Section: Packing Methods”.
- These packages are not suitable for wave soldering. On versions with the heatsink on the bottom side, the solder cannot penetrate between the printed-circuit board and the heatsink. On versions with the heatsink on the top side, the solder might be deposited on the heatsink surface.
- If wave soldering is considered, then the package must be placed at a 45° angle to the solder wave direction. The package footprint must incorporate solder thieves downstream and at the side corners.
- Wave soldering is suitable for LQFP, TQFP and QFP packages with a pitch (e) larger than 0.8 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.65 mm.
- Wave soldering is suitable for SSOP, TSSOP, VSO and VSSOP packages with a pitch (e) equal to or larger than 0.65 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.5 mm.

Dual buffer/line driver with 5 V tolerant inputs/outputs; 3-state

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DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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Dual buffer/line driver with 5 V
tolerant inputs/outputs; 3-state

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NOTES

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